

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

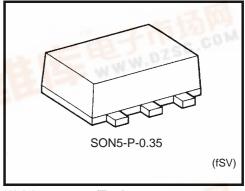
# TC7SH86FS

#### **EXCLUSIVE OR GATE**

#### **Features**

High speed:  $t_{pd}$  = 4.8 ns (typ.) at  $V_{CC}$  = 5 V Low power dissipation:  $I_{CC}$  = 2  $\mu$ A (max) at Ta = 25°C High noise immunity:  $V_{NIH}$  =  $V_{NIL}$  = 28%  $V_{CC}$  (min) 5.5V tolerant input.

Wide operating voltage range:  $V_{CC}$  (opr) = 2~5.5 V

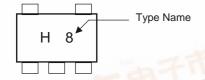


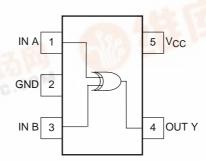
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# Marking (top view)

### Pin Assignment









## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	−0.5~V <sub>CC</sub> + 0.5	٧
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Logic Diagram**



### **Truth Table**

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	٧
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~Vcc	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V <sub>CC</sub> = 3.3 ± 0.3 V)	ns/V
	ui/uv	0~20 (V <sub>CC</sub> = 5 ± 0.5 V)	115/ V

## **Electrical Characteristics**

### **DC Characteristics**

Characteristics Symbol Test Circuit		Test				7	Га = 25°(		Ta = -40~85°C		
		Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit	
High-level input VIH —						1.50		_	1.50	_	V
		_		3.0~ 5.5	V <sub>CC</sub> × 0.7		_	V <sub>CC</sub> × 0.7			
Low lovel input					2.0	_		0.50	_	0.50	
Low-level input voltage V <sub>IL</sub> —	_	_		3.0~ 5.5	_		V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> × 0.3	V	
				Ι <sub>ΟΗ</sub> = -50 μΑ	2.0	1.9	2.0	_	1.9	_	V
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		3.0	2.9	3.0	_	2.9	_	
High-level output voltage	V <sub>OH</sub>				4.5	4.4	4.5	_	4.4		
, and an armage				I <sub>OH</sub> = -4 mA	3.0	2.58		_	2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94		_	3.80		
					2.0	_	0.0	0.1	_	0.1	
Low-level output voltage	_	$V_{IN} = V_{IL}$	I <sub>OL</sub> = 50 μA	3.0	_	0.0	0.1	_	0.1	V	
				4.5	_	0.0	0.1	_	0.1		
				I <sub>OL</sub> = 4 mA	3.0			0.36		0.44	
				I <sub>OL</sub> = 8 mA	4.5	_		0.36	_	0.44	
Input leakage current	I <sub>IN</sub>	_	V <sub>IN</sub> = 5.5 V or GND			_		±0.1	_	±1.0	μА
Quiescent supply current	Icc	_	V <sub>IN</sub> = V <sub>CC</sub> or GND			_	_	2.0	_	20.0	μА

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### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics S	Symbol	Test Circuit	Test Conditio		n ·		Ta = 25°C		Ta = -40~85°C		Unit
	Symbol			V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time				0.0.1.0.0	15	_	7.0	11.0	1.0	13.0	
	$\mathrm{t_{pLH}}$			$3.3 \pm 0.3$	50	_	9.5	14.5	1.0	16.5	
	${ m t}_{ m pHL}$	_		5.0 ± 0.5	15	_	4.8	6.8	1.0	8.0	ns
					50	_	6.3	8.8	1.0	10.0	
Input capacitance	C <sub>IN</sub>	_		_		_	4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>	_			(Note)	_	18	_	_	_	pF

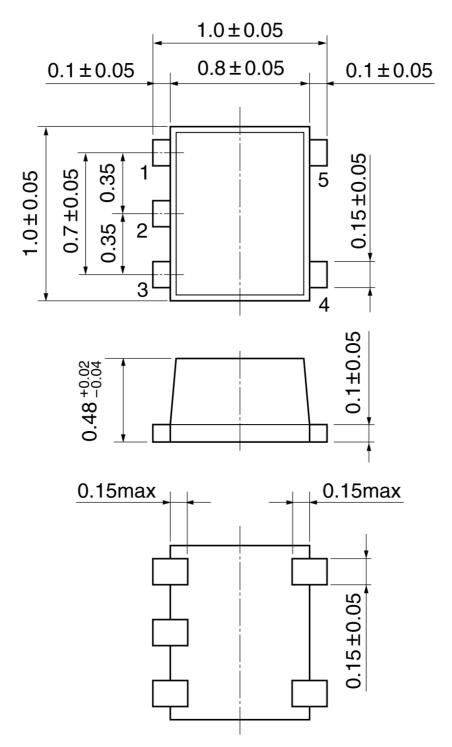
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

## **Package Dimensions**

SON5-P-0.35 Unit:mm



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Weight: 0.001 g (typ.)

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